

2SA1523/2SC3917**Switching Applications (with Bias Resistance)****Applications**

- Switching circuits, inverter circuits, interface circuits, driver circuits.

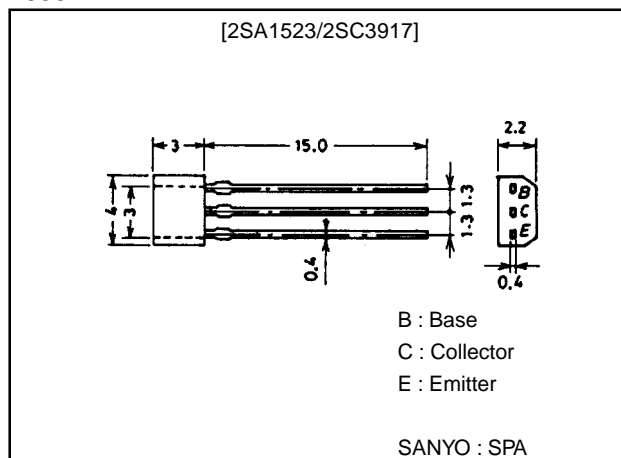
Features

- On-chip bias resistance : $R_1=4.7k\Omega$, $R_2=4.7k\Omega$.
- Small-sized package : SPA.
- Large current capacity : $I_C=500mA$.

Package Dimensions

unit:mm

2033



() : 2SA1523

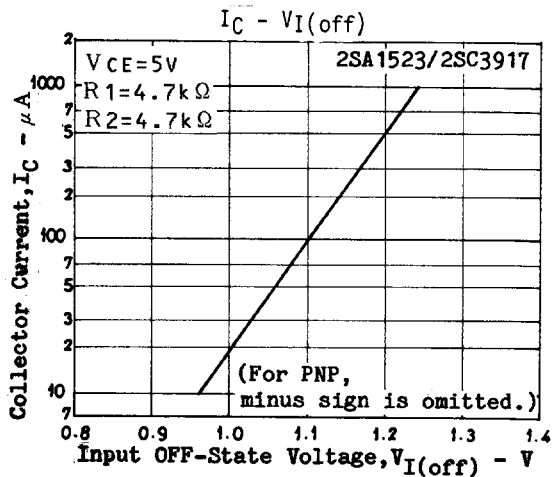
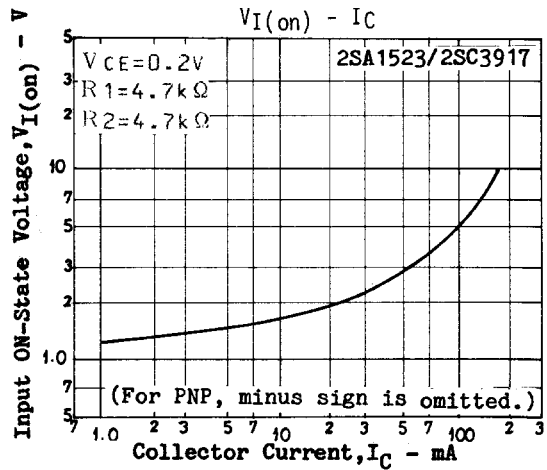
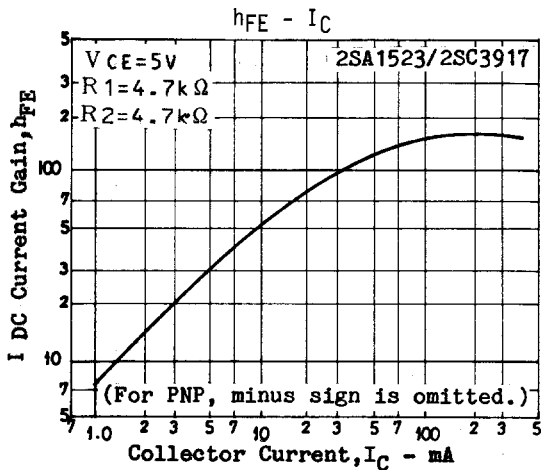
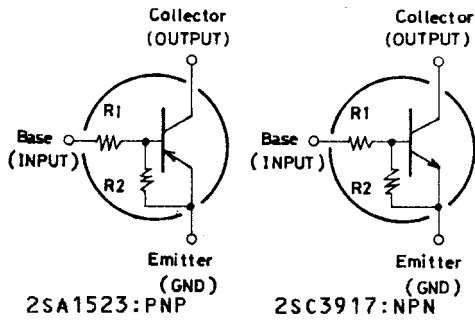
Specifications**Absolute Maximum Ratings at $T_a = 25^\circ C$**

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)-50	V
Collector-to-Emitter Voltage	V_{CEO}		(-)-50	V
Emitter-to-Base Voltage	V_{EBO}		(-)-6	V
Collector Current	I_C		(-)-500	mA
Collector Current (Pulse)	I_{CP}		(-)-800	mA
Collector Dissipation	P_C		300	mW
Junction Temperature	T_j		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0$			(-)-0.1	μA
	I_{CEO}	$V_{CE}=(-)40V, I_B=0$			(-)-0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5V, I_C=0$	(-)-410	(-)-532	(-)-760	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)5V, I_C=(-)20mA$	50			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)5mA$		250		MHz
				(200)		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10V, f=1MHz$		3.7		pF
				(5.5)		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)40mA, I_B=(-)2mA$		(-)-0.1	(-)-0.3	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)-50			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)100\mu A, R_{BE}=\infty$	(-)-50			V
Input OFF-State Voltage	$V_{I(off)}$	$V_{CE}=(-)5V, I_C=(-)100\mu A$	(-)-0.8	(-)-1.1	(-)-1.5	V
Input ON-State Voltage	$V_{I(on)}$	$V_{CE}=(-)0.2V, I_C=(-)20mA$	(-)-1.0	(-)-1.9	(-)-4.0	V
Input Resistance	R_1		3.3	4.7	6.1	$k\Omega$
Resistance Ratio	R_1/R_2		0.9	1.0	1.1	

Electrical Connection



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